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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	I <sup>2</sup> C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, Motor Control PWM, QEI, POR, PWM, WDT
Number of I/O	30
Program Memory Size	24KB (8K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	44-VQFN Exposed Pad
Supplier Device Package	44-QFN (8x8)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/dspic30f3011t-20e-ml">https://www.e-xfl.com/product-detail/microchip-technology/dspic30f3011t-20e-ml</a>

# dsPIC30F Flash Programming Specification

## 2.2 Pins Used During Programming

The pins identified in [Table 2-1](#) are used for device programming. Refer to the appropriate device data sheet for complete pin descriptions.

**TABLE 2-1: dsPIC30F PIN DESCRIPTIONS DURING PROGRAMMING**

Pin Name	Pin Type	Pin Description
MCLR/VPP	P	Programming Enable
VDD	P	Power Supply
VSS	P	Ground
PGC	I	Serial Clock
PGD	I/O	Serial Data

**Legend:** I = Input, O = Output, P = Power

## 2.3 Program Memory Map

The program memory space extends from 0x0 to 0xFFFFFE. Code storage is located at the base of the memory map and supports up to 144 Kbytes (48K instruction words). Code is stored in three, 48 Kbyte memory panels that reside on-chip. [Table 2-2](#) shows the location and program memory size of each device.

Locations 0x800000 through 0x8005BE are reserved for executive code memory. This region stores either the programming executive or debugging executive. The programming executive is used for device programming, while the debug executive is used for in-circuit debugging. This region of memory cannot be used to store user code.

Locations 0xF80000 through 0xF8000E are reserved for the Configuration registers. The bits in these registers may be set to select various device options, and are described in [Section 5.7 “Configuration Bits Programming”](#).

Locations 0xFF0000 and 0xFF0002 are reserved for the Device ID registers. These bits can be used by the programmer to identify what device type is being programmed and are described in [Section 10.0 “Device ID”](#). The device ID reads out normally, even after code protection is applied.

[Figure 2-2](#) illustrates the memory map for the dsPIC30F devices.

## 2.4 Data EEPROM Memory

The Data EEPROM array supports up to 4 Kbytes of data and is located in one memory panel. It is mapped in program memory space, residing at the end of User Memory Space (see [Figure 2-2](#)). [Table 2-2](#) shows the location and size of data EEPROM in each device.

**TABLE 2-2: CODE MEMORY AND DATA EEPROM MAP AND SIZE**

Device	Code Memory map (Size in Instruction Words)	Data EEPROM Memory Map (Size in Bytes)
dsPIC30F2010	0x000000-0x001FFE (4K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F2011	0x000000-0x001FFE (4K)	None (0K)
dsPIC30F2012	0x000000-0x001FFE (4K)	None (0K)
dsPIC30F3010	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3011	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3012	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3013	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3014	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F4011	0x000000-0x007FFE (16K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F4012	0x000000-0x007FFE (16K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F4013	0x000000-0x007FFE (16K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5011	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5013	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5015	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5016	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F6010	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6010A	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFF (4K)
dsPIC30F6011	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6011A	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6012	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6012A	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6013	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6013A	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6014	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6014A	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6015	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)

# dsPIC30F Flash Programming Specification

## 3.0 PROGRAMMING EXECUTIVE APPLICATION

### 3.1 Programming Executive Overview

The programming executive resides in executive memory and is executed when Enhanced ICSP Programming mode is entered. The programming executive provides the mechanism for the programmer (host device) to program and verify the dsPIC30F, using a simple command set and communication protocol.

The following capabilities are provided by the programming executive:

- Read memory
  - Code memory and data EEPROM
  - Configuration registers
  - Device ID
- Erase memory
  - Bulk Erase by segment
  - Code memory (by row)
  - Data EEPROM (by row)
- Program memory
  - Code memory
  - Data EEPROM
  - Configuration registers
- Query
  - Blank Device
  - Programming executive software version

The programming executive performs the low-level tasks required for erasing and programming. This allows the programmer to program the device by issuing the appropriate commands and data.

The programming procedure is outlined in [Section 5.0 “Device Programming”](#).

### 3.2 Programming Executive Code Memory

The programming executive is stored in executive code memory and executes from this reserved region of memory. It requires no resources from user code memory or data EEPROM.

### 3.3 Programming Executive Data RAM

The programming executive uses the device's data RAM for variable storage and program execution. Once the programming executive has run, no assumptions should be made about the contents of data RAM.

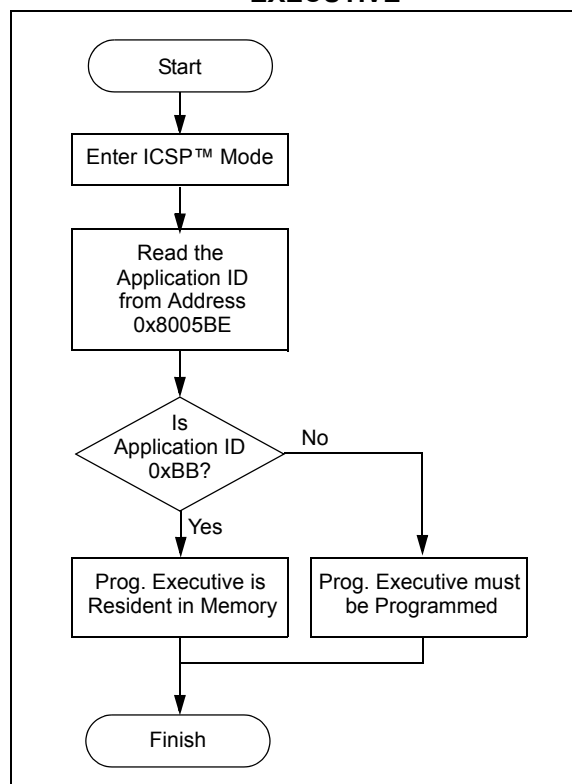
## 4.0 CONFIRMING THE CONTENTS OF EXECUTIVE MEMORY

Before programming can begin, the programmer must confirm that the programming executive is stored in executive memory. The procedure for this task is illustrated in [Figure 4-1](#).

First, ICSP mode is entered. The unique application ID word stored in executive memory is then read. If the programming executive is resident, the application ID word is 0xBB, which means programming can resume as normal. However, if the application ID word is not 0xBB, the programming executive must be programmed to Executive Code memory using the method described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

[Section 11.0 “ICSP™ Mode”](#) describes the process for the ICSP programming method. [Section 11.13 “Reading the Application ID Word”](#) describes the procedure for reading the application ID word in ICSP mode.

**FIGURE 4-1: CONFIRMING PRESENCE OF THE PROGRAMMING EXECUTIVE**



# dsPIC30F Flash Programming Specification

## 5.0 DEVICE PROGRAMMING

### 5.1 Overview of the Programming Process

Once the programming executive has been verified in memory (or loaded if not present), the dsPIC30F can be programmed using the command set shown in [Table 5-1](#). A detailed description for each command is provided in [Section 8.0 “Programming Executive Commands”](#).

**TABLE 5-1: COMMAND SET SUMMARY**

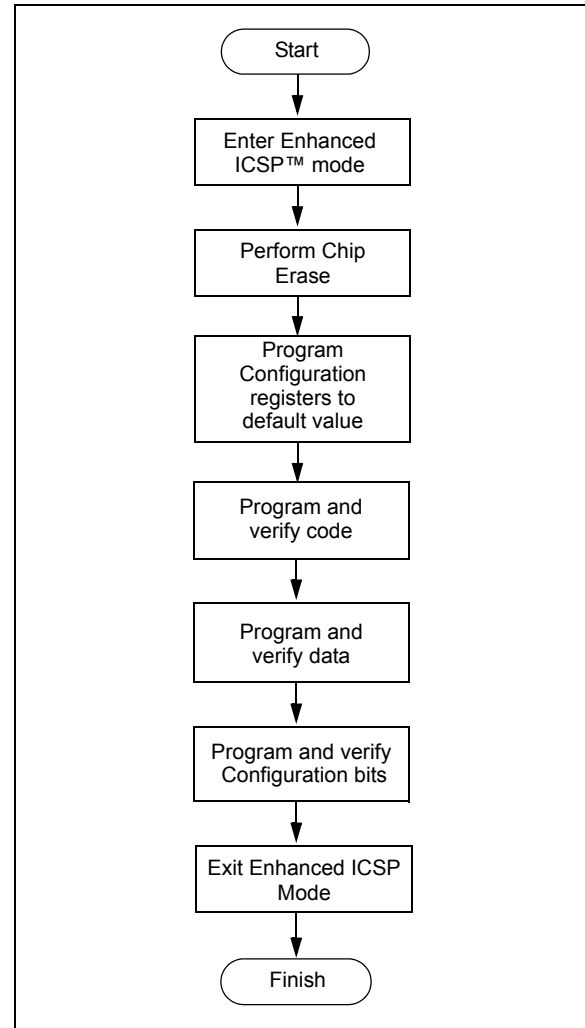
Command	Description
SCHECK	Sanity check
READD	Read data EEPROM, Configuration registers and device ID
READP	Read code memory
PROGD	Program one row of data EEPROM and verify
PROGP	Program one row of code memory and verify
PROGC	Program Configuration bits and verify
ERASEB	Bulk Erase, or erase by segment
ERASED	Erase data EEPROM
ERASEP	Erase code memory
QBLANK	Query if the code memory and data EEPROM are blank
QVER	Query the software version

A high-level overview of the programming process is illustrated in [Figure 5-1](#). The process begins by entering Enhanced ICSP mode. The chip is then bulk erased, which clears all memory to ‘1’ and allows the device to be programmed. The Chip Erase is verified before programming begins. Next, the code memory, data Flash and Configuration bits are programmed. As these memories are programmed, they are each verified to ensure that programming was successful. If no errors are detected, the programming is complete and Enhanced ICSP mode is exited. If any of the verifications fail, the procedure should be repeated, starting from the Chip Erase.

If Advanced Security features are enabled, then individual Segment Erase operations need to be performed, based on user selections (i.e., based on the specific needs of the user application). The specific operations that are used typically depend on the order in which various segments need to be programmed for a given application or system.

[Section 5.2 “Entering Enhanced ICSP Mode”](#) through [Section 5.8 “Exiting Enhanced ICSP Mode”](#) describe the programming process in detail.

**FIGURE 5-1: PROGRAMMING FLOW**



# dsPIC30F Flash Programming Specification

## 5.5 Code Memory Programming

### 5.5.1 OVERVIEW

The Flash code memory array consists of 512 rows of thirty-two, 24-bit instructions. Each panel stores 16K instruction words, and each dsPIC30F device has either 1, 2 or 3 memory panels (see [Table 5-2](#)).

**TABLE 5-2: DEVICE CODE MEMORY SIZE**

Device	Code Size (24-bit Words)	Number of Rows	Number of Panels
dsPIC30F2010	4K	128	1
dsPIC30F2011	4K	128	1
dsPIC30F2012	4K	128	1
dsPIC30F3010	8K	256	1
dsPIC30F3011	8K	256	1
dsPIC30F3012	8K	256	1
dsPIC30F3013	8K	256	1
dsPIC30F3014	8K	256	1
dsPIC30F4011	16K	512	1
dsPIC30F4012	16K	512	1
dsPIC30F4013	16K	512	1
dsPIC30F5011	22K	704	2
dsPIC30F5013	22K	704	2
dsPIC30F5015	22K	704	2
dsPIC30F5016	22K	704	2
dsPIC30F6010	48K	1536	3
dsPIC30F6010A	48K	1536	3
dsPIC30F6011	44K	1408	3
dsPIC30F6011A	44K	1408	3
dsPIC30F6012	48K	1536	3
dsPIC30F6012A	48K	1536	3
dsPIC30F6013	44K	1408	3
dsPIC30F6013A	44K	1408	3
dsPIC30F6014	48K	1536	3
dsPIC30F6014A	48K	1536	3
dsPIC30F6015	48K	1536	3

### 5.5.2 PROGRAMMING METHODOLOGY

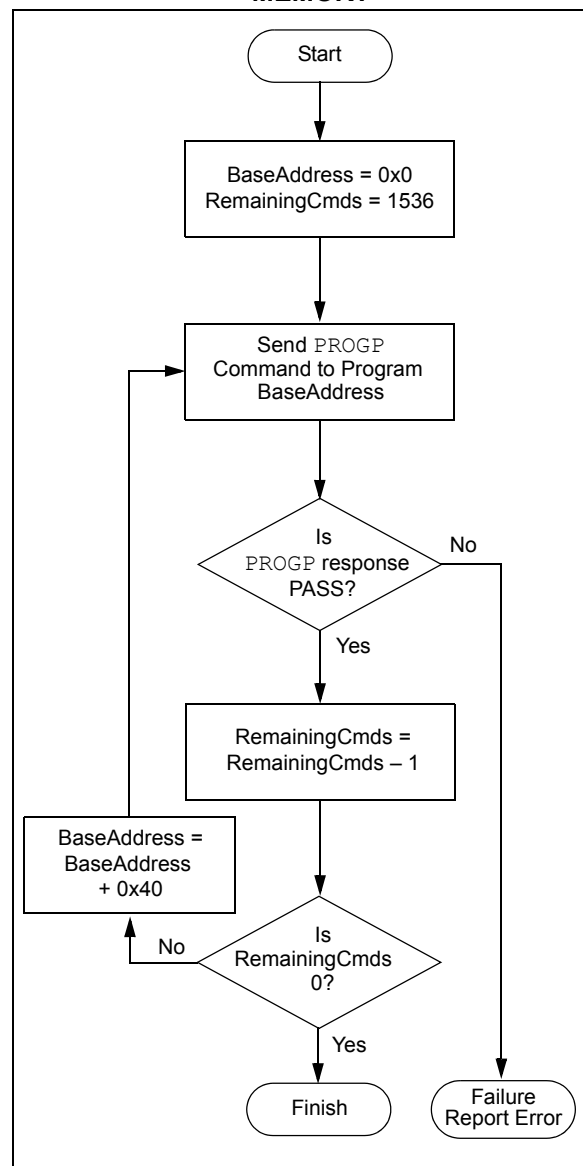
Code memory is programmed with the `PROGP` command. `PROGP` programs one row of code memory to the memory address specified in the command. The number of `PROGP` commands required to program a device depends on the number of rows that must be programmed in the device.

A flowchart for programming of code memory is illustrated in [Figure 5-3](#). In this example, all 48K instruction words of a dsPIC30F6014A device are programmed. First, the number of commands to send (called 'RemainingCmds' in the flowchart) is set to 1536 and the destination address (called 'BaseAddress') is set to '0'.

Next, one row in the device is programmed with a `PROGP` command. Each `PROGP` command contains data for one row of code memory of the dsPIC30F6014A. After the first command is processed successfully, 'RemainingCmds' is decremented by 1 and compared to 0. Since there are more `PROGP` commands to send, 'BaseAddress' is incremented by 0x40 to point to the next row of memory.

On the second `PROGP` command, the second row of each memory panel is programmed. This process is repeated until the entire device is programmed. No special handling must be performed when a panel boundary is crossed.

**FIGURE 5-3: FLOWCHART FOR PROGRAMMING dsPIC30F6014A CODE MEMORY**



# dsPIC30F Flash Programming Specification

## 5.6.3 PROGRAMMING VERIFICATION

Once the data EEPROM is programmed, the contents of memory can be verified to ensure that the programming was successful. Verification requires the data EEPROM to be read back and compared against the copy held in the programmer's buffer. The `READD` command reads back the programmed data EEPROM.

Alternatively, the programmer can perform the verification once the entire device is programmed using a checksum computation, as described in [Section 6.8 "Checksum Computation"](#).

**Note:** `TBLRDL` instructions executed within a `REPEAT` loop must not be used to read from Data EEPROM. Instead, it is recommended to use PSV access.

## 5.7 Configuration Bits Programming

### 5.7.1 OVERVIEW

The dsPIC30F has Configuration bits stored in seven 16-bit registers. These bits can be set or cleared to select various device configurations. There are two types of Configuration bits: system-operation bits and code-protect bits. The system-operation bits determine the power-on settings for system-level components such as the oscillator and Watchdog Timer. The code-protect bits prevent program memory from being read and written.

The FOSC Configuration register has three different register descriptions, based on the device. The FOSC Configuration register description for the dsPIC30F2010 and dsPIC30F6010/6011/6012/6013/6014 devices are shown in [Table 5-4](#).

**Note:** If user software performs an erase operation on the configuration fuse, it must be followed by a write operation to this fuse with the desired value, even if the desired value is the same as the state of the erased fuse.

The FOSC Configuration register description for the dsPIC30F4011/4012 and dsPIC30F5011/5013 devices is shown in [Table 5-5](#).

The FOSC Configuration register description for all remaining devices (dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013, dsPIC30F3014/4013, dsPIC30F5015 and dsPIC30F6011A/6012A/6013A/6014A) is shown in [Table 5-6](#). Always use the correct register descriptions for your target processor.

The `FWDT`, `FBORPOR`, `FBS`, `FSS`, `FGS` and `FICD` Configuration registers are not device-dependent. The register descriptions for these Configuration registers are shown in [Table 5-7](#).

The Device Configuration register maps are shown in [Table 5-8](#) through [Table 5-11](#).

**TABLE 5-4: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2010 AND dsPIC30F6010/6011/6012/6013/6014**

Bit Field	Register	Description
FCKSM<1:0>	FOSC	<b>Clock Switching Mode</b> 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<1:0>	FOSC	<b>Oscillator Source Selection on POR</b> 11 = Primary Oscillator 10 = Internal Low-Power RC Oscillator 01 = Internal Fast RC Oscillator 00 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<3:0>	FOSC	<b>Primary Oscillator Mode</b> 1111 = ECIO w/PLL 16X – External Clock mode with 16X PLL. OSC2 pin is I/O 1110 = ECIO w/PLL 8X – External Clock mode with 8X PLL. OSC2 pin is I/O 1101 = ECIO w/PLL 4X – External Clock mode with 4X PLL. OSC2 pin is I/O 1100 = ECIO – External Clock mode. OSC2 pin is I/O 1011 = EC – External Clock mode. OSC2 pin is system clock output (Fosc/4) 1010 = Reserved (do not use) 1001 = ERC – External RC Oscillator mode. OSC2 pin is system clock output (Fosc/4) 1000 = ERCIO – External RC Oscillator mode. OSC2 pin is I/O 0111 = XT w/PLL 16X – XT Crystal Oscillator mode with 16X PLL 0110 = XT w/PLL 8X – XT Crystal Oscillator mode with 8X PLL 0101 = XT w/PLL 4X – XT Crystal Oscillator mode with 4X PLL 0100 = XT – XT Crystal Oscillator mode (4 MHz-10 MHz crystal) 001x = HS – HS Crystal Oscillator mode (10 MHz-25 MHz crystal) 000x = XTL – XTL Crystal Oscillator mode (200 kHz-4 MHz crystal)

# dsPIC30F Flash Programming Specification

**TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015 (CONTINUED)**

Bit Field	Register	Description
FPR<4:0>	FOSC	<b>Alternate Oscillator Mode (when FOS&lt;2:0&gt; = 011b)</b> 1xxxx = Reserved (do not use) 0111x = Reserved (do not use) 01101 = Reserved (do not use) 01100 = ECIO – External clock. OSC2 pin is I/O 01011 = EC – External clock. OSC2 pin is system clock output (Fosc/4) 01010 = Reserved (do not use) 01001 = ERC – External RC oscillator. OSC2 pin is system clock output (Fosc/4) 01000 = ERCIO – External RC oscillator. OSC2 pin is I/O 00111 = Reserved (do not use) 00110 = Reserved (do not use) 00101 = Reserved (do not use) 00100 = XT – XT crystal oscillator (4 MHz-10 MHz crystal) 00010 = HS – HS crystal oscillator (10 MHz-25 MHz crystal) 00001 = Reserved (do not use) 00000 = XTL – XTL crystal oscillator (200 kHz-4 MHz crystal)

# dsPIC30F Flash Programming Specification

**TABLE 5-7: CONFIGURATION BITS DESCRIPTION**

Bit Field	Register	Description
FWPSA<1:0>	FWDT	<b>Watchdog Timer Prescaler A</b> 11 = 1:512 10 = 1:64 01 = 1:8 00 = 1:1
FWPSB<3:0>	FWDT	<b>Watchdog Timer Prescaler B</b> 1111 = 1:16 1110 = 1:15 . . . 0001 = 1:2 0000 = 1:1
FWDTEN	FWDT	<b>Watchdog Enable</b> 1 = Watchdog enabled (LPRC oscillator cannot be disabled. Clearing the SWDTEN bit in the RCON register will have no effect) 0 = Watchdog disabled (LPRC oscillator can be disabled by clearing the SWDTEN bit in the RCON register)
MCLREN	FBORPOR	<b>Master Clear Enable</b> 1 = Master Clear pin (MCLR) is enabled 0 = MCLR pin is disabled
PWMPIN	FBORPOR	<b>Motor Control PWM Module Pin Mode</b> 1 = PWM module pins controlled by PORT register at device Reset (tri-stated) 0 = PWM module pins controlled by PWM module at device Reset (configured as output pins)
HPOL	FBORPOR	<b>Motor Control PWM Module High-Side Polarity</b> 1 = PWM module high-side output pins have active-high output polarity 0 = PWM module high-side output pins have active-low output polarity
LPOL	FBORPOR	<b>Motor Control PWM Module Low-Side Polarity</b> 1 = PWM module low-side output pins have active-high output polarity 0 = PWM module low-side output pins have active-low output polarity
BOREN	FBORPOR	<b>PBOR Enable</b> 1 = PBOR enabled 0 = PBOR disabled
BORV<1:0>	FBORPOR	<b>Brown-out Voltage Select</b> 11 = 2.0V (not a valid operating selection) 10 = 2.7V 01 = 4.2V 00 = 4.5V
FPWRT<1:0>	FBORPOR	<b>Power-on Reset Timer Value Select</b> 11 = PWRT = 64 ms 10 = PWRT = 16 ms 01 = PWRT = 4 ms 00 = Power-up Timer disabled
RBS<1:0>	FBS	<b>Boot Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 11 = No Data RAM is reserved for Boot Segment 10 = Small-sized Boot RAM [128 bytes of RAM are reserved for Boot Segment] 01 = Medium-sized Boot RAM [256 bytes of RAM are reserved for Boot Segment] 00 = Large-sized Boot RAM [512 bytes of RAM are reserved for Boot Segment in dsPIC30F5011/5013, and 1024 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015]



**TABLE 5-10: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013 AND dsPIC30F5015/5016)**

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	FOS<2:0>			—	—	—	FPR<4:0>				
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN <sup>(1)</sup>	HPOL <sup>(1)</sup>	LPOL <sup>(1)</sup>	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	Reserved <sup>(2)</sup>		—	—	—	Reserved <sup>(2)</sup>	—	—	—	—	Reserved <sup>(2)</sup>			
0xF80008	FSS	—	—	Reserved <sup>(2)</sup>		—	—	Reserved <sup>(2)</sup>		—	—	—	—	Reserved <sup>(2)</sup>			
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	Reserved <sup>(3)</sup>	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

**Note** 1: On the 2011, 2012, 3012, 3013, 3014 and 4013, these bits are reserved (read as '1' and must be programmed as '1').  
2: Reserved bits read as '1' and must be programmed as '1'.  
3: The FGS<2> bit is a read-only copy of the GCP bit (FGS<1>).

**TABLE 5-11: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015)**

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	FOS<2:0>			—	—	—	FPR<4:0>				
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN <sup>(1)</sup>	HPOL <sup>(1)</sup>	LPOL <sup>(1)</sup>	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	RBS<1:0>		—	—	—	EBS	—	—	—	—	BSS<2:0>			BWRP
0xF80008	FSS	—	—	RSS<1:0>		—	—	ESS<1:0>		—	—	—	—	SSS<2:0>			SWRP
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	GSS<1:0>		GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

**Note** 1: On the 6011A, 6012A, 6013A and 6014A, these bits are reserved (read as '1' and must be programmed as '1').

# dsPIC30F Flash Programming Specification

## 6.0 OTHER PROGRAMMING FEATURES

### 6.1 Erasing Memory

Memory is erased by using an `ERASEB`, `ERASED` or `ERASEP` command, as detailed in [Section 8.5 “Command Descriptions”](#). Code memory can be erased by row using `ERASEP`. Data EEPROM can be erased by row using `ERASED`. When memory is erased, the affected memory locations are set to ‘1’s.

`ERASEB` provides several Bulk Erase options. Performing a Chip Erase with the `ERASEB` command clears all code memory, data EEPROM and code protection registers. Alternatively, `ERASEB` can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in [Table 6-1](#).

**TABLE 6-1: ERASE OPTIONS**

Command	Affected Region
<code>ERASEB</code>	Entire chip <sup>(1)</sup> or all code memory or all data EEPROM, or erase by segment
<code>ERASED</code>	Specified rows of data EEPROM
<code>ERASEP</code> <sup>(2)</sup>	Specified rows of code memory

- Note 1:** The system operation Configuration registers and device ID registers are not erasable.
- 2:** `ERASEP` cannot be used to erase code-protect Configuration bits. These bits must be erased using `ERASEB`.

### 6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using `ERASEP` and `ERASED`, respectively. You can then reprogram the modified rows with the `PROGP` and `PROGD` command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the `PROGP` command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the `ERASEB` command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select)

field in the `ERASEB` command. The code-protect Configuration bits can then be reprogrammed using the `PROGC` command.

**Note:** If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

### 6.3 Reading Memory

The `READD` command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. `READD` can be used to return the entire contents of data EEPROM.

The `READP` command reads the code memory of the device. This command only returns 24-bit data packed as described in [Section 8.3 “Packed Data Format”](#). `READP` can be used to read up to 32K instruction words of code memory.

**Note:** Reading an unimplemented memory location causes the programming executive to reset. All `READD` and `READP` commands **must** specify only valid memory locations.

### 6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The `QVER` command performs this function. See [Section 8.5.11 “QVER Command”](#) for more details about this command.

### 6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

# dsPIC30F Flash Programming Specification

## 8.0 PROGRAMMING EXECUTIVE COMMANDS

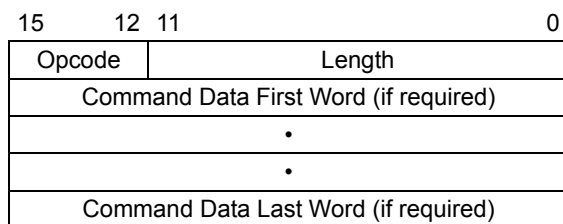
### 8.1 Command Set

The programming executive command set is shown in [Table 8-1](#). This table contains the opcode, mnemonic, length, time out and description for each command. Functional details on each command are provided in the command descriptions (see [Section 8.5 “Command Descriptions”](#)).

### 8.2 Command Format

All programming executive commands have a general format consisting of a 16-bit header and any required data for the command (see [Figure 8-1](#)). The 16-bit header consists of a 4-bit opcode field, which is used to identify the command, followed by a 12-bit command length field.

**FIGURE 8-1: COMMAND FORMAT**



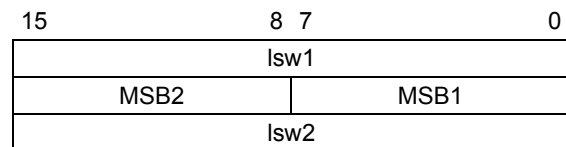
The command opcode must match one of those in the command set. Any command that is received which does not match the list in [Table 8-1](#) will return a “NACK” response (see [Section 9.2.1 “Opcode Field”](#)).

The command length is represented in 16-bit words since the SPI operates in 16-bit mode. The programming executive uses the Command Length field to determine the number of words to read from the SPI port. If the value of this field is incorrect, the command will not be properly received by the programming executive.

### 8.3 Packed Data Format

When 24-bit instruction words are transferred across the 16-bit SPI interface, they are packed to conserve space using the format shown in [Figure 8-2](#). This format minimizes traffic over the SPI and provides the programming executive with data that is properly aligned for performing table write operations.

**FIGURE 8-2: PACKED INSTRUCTION WORD FORMAT**



lswx: Least significant 16 bits of instruction word

MSBx: Most Significant Byte of instruction word

**Note:** When the number of instruction words transferred is odd, MSB2 is zero and lsw2 cannot be transmitted.

### 8.4 Programming Executive Error Handling

The programming executive will “NACK” all unsupported commands. Additionally, due to the memory constraints of the programming executive, no checking is performed on the data contained in the Programmer command. It is the responsibility of the programmer to command the programming executive with valid command arguments, or the programming operation may fail. Additional information on error handling is provided in [Section 9.2.3 “QE\\_Code Field”](#).

# dsPIC30F Flash Programming Specification

## 8.5.11 QVER COMMAND

15	12	11	0
Opcode		Length	

Field	Description
Opcode	0xB
Length	0x1

The QVER command queries the version of the programming executive software stored in test memory. The “version.revision” information is returned in the response’s QE\_Code using a single byte with the following format: main version in upper nibble and revision in the lower nibble (i.e., 0x23 is version 2.3 of programming executive software).

### Expected Response (2 words):

0x1BMN (where “MN” stands for version M.N)  
0x0002

## 9.0 PROGRAMMING EXECUTIVE RESPONSES

### 9.1 Overview

The programming executive sends a response to the programmer for each command that it receives. The response indicates if the command was processed correctly, and includes any required response or error data.

The programming executive response set is shown in Table 9-1. This table contains the opcode, mnemonic and description for each response. The response format is described in Section 9.2 “Response Format”.

**TABLE 9-1: PROGRAMMING EXECUTIVE RESPONSE SET**

Opcode	Mnemonic	Description
0x1	PASS	Command successfully processed.
0x2	FAIL	Command unsuccessfully processed.
0x3	NACK	Command not known.

## 9.2 Response Format

As shown in Example 9-1, all programming executive responses have a general format consisting of a two word header and any required data for the command. Table 9-2 lists the fields and their descriptions.

**EXAMPLE 9-1: FORMAT**

15	12	11	8	7	0
Opcode	Last_Cmd	QE_Code			
Length					
D_1 (if applicable)					
...					
D_N (if applicable)					

**TABLE 9-2: FIELDS AND DESCRIPTIONS**

Field	Description
Opcode	Response opcode.
Last_Cmd	Programmer command that generated the response.
QE_Code	Query code or Error code.
Length	Response length in 16-bit words (includes 2 header words.)
D_1	First 16-bit data word (if applicable).
D_N	Last 16-bit data word (if applicable).

### 9.2.1 Opcode FIELD

The Opcode is a 4-bit field in the first word of the response. The Opcode indicates how the command was processed (see Table 9-1). If the command is processed successfully, the response opcode is PASS. If there is an error in processing the command, the response opcode is FAIL, and the QE\_Code indicates the reason for the failure. If the command sent to the programming executive is not identified, the programming executive returns a NACK response.

### 9.2.2 Last\_Cmd FIELD

The Last\_Cmd is a 4-bit field in the first word of the response and indicates the command that the programming executive processed. Since the programming executive can only process one command at a time, this field is technically not required. However, it can be used to verify whether the programming executive correctly received the command that the programmer transmitted.

# dsPIC30F Flash Programming Specification

Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

**Note:** Program memory must be erased before writing any data to program memory.

**TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Set NVMCON to program the FBS Configuration register.<sup>(1)</sup></b>		
0000	24008A	MOV #0x4008, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 3: Initialize the TBLPAG and write pointer (W7) for TBLWT instruction for Configuration register.<sup>(1)</sup></b>		
0000	200F80	MOV #0xF8, W0
0000	880190	MOV W0, TBLPAG
0000	200067	MOV #0x6, W7
<b>Step 4: Load the Configuration Register data to W6.<sup>(1)</sup></b>		
0000	EB0300	CLR W6
0000	000000	NOP
<b>Step 5: Load the Configuration Register write latch. Advance W7 to point to next Configuration register.<sup>(1)</sup></b>		
0000	BB1B86	TBLWTL W6, [W7++]
<b>Step 6: Unlock the NVMCON for programming the Configuration register.<sup>(1)</sup></b>		
0000	200558	MOV #0x55, W8
0000	200AA9	MOV #0xAA, W9
0000	883B38	MOV W8, NVMKEY
0000	883B39	MOV W9, NVMKEY
<b>Step 7: Initiate the programming cycle.<sup>(1)</sup></b>		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 2 ms
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 8: Repeat steps 5-7 one time to program 0x0000 to RESERVED2 Configuration register.<sup>(1)</sup></b>		
<b>Step 9: Set the NVMCON to erase all Program Memory.</b>		
00000	2407FA	MOV #0x407F, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 10: Unlock the NVMCON for programming.</b>		

**Note 1:** Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

# dsPIC30F Flash Programming Specification

**TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY  
(EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 6:</b> Update the row address stored in NVMADRU:NVMADR. When W6 rolls over to 0x0, NVMADRU must be incremented.		
0000	430307	ADD W6, W7, W6
0000	AF0042	BTSC SR, #C
0000	EC2764	INC NVMADRU
0000	883B16	MOV W6, NVMADR
<b>Step 7:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 8:</b> Repeat Steps 3-7 until all rows of code memory are erased.		
<b>Step 9:</b> Initialize NVMADR and NVMADRU to erase executive memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	200807	MOV #0x80, W7
0000	883B27	MOV W7, NVMADRU
0000	200407	MOV #0x40, W7
<b>Step 10:</b> Set NVMCON to erase 1 row of executive memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 11:</b> Unlock the NVMCON to erase 1 row of executive memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 12:</b> Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 13:</b> Update the row address stored in NVMADR.		
0000	430307	ADD W6, W7, W6
0000	883B16	MOV W6, NVMADR
<b>Step 14:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 15:</b> Repeat Steps 10-14 until all 24 rows of executive memory are erased.		
<b>Step 16:</b> Initialize NVMADR and NVMADRU to erase data memory and initialize W7 for row address updates.		
0000	2XXXX6	MOV #<lower 16-bits of starting Data EEPROM address>, W6
0000	883B16	MOV W6, NVMADR
0000	2007F6	MOV #0x7F, W6
0000	883B16	MOV W6, NVMADRU
0000	200207	MOV #0x20, W7
<b>Step 17:</b> Set NVMCON to erase 1 row of data memory.		
0000	24075A	MOV #0x4075, W10
0000	883B0A	MOV W10, NVMCON

# dsPIC30F Flash Programming Specification

**TABLE 11-7: SERIAL INSTRUCTION EXECUTION FOR WRITING CONFIGURATION REGISTERS (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 6:</b> Write the Configuration register data to the write latch and increment the write pointer.		
0000	BB1B96	TBLWTL W6, [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 7:</b> Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 8:</b> Initiate the write cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 9:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 10:</b> Repeat steps 3-9 until all 7 Configuration registers are cleared.		

# dsPIC30F Flash Programming Specification

**TABLE 11-10: SERIAL INSTRUCTION EXECUTION FOR READING CODE MEMORY (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 4: Output W0:W5 using the VISI register and REGOUT command.</b>		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C24	MOV W4, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C25	MOV W5, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
<b>Step 5: Reset the device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6: Repeat steps 3-5 until all desired code memory is read.</b>		



# dsPIC30F Flash Programming Specification

## 11.11 Reading Configuration Memory

The procedure for reading configuration memory is similar to the procedure for reading code memory, except that 16-bit data words are read instead of 24-bit words. Since there are seven Configuration registers, they are read one register at a time.

Table 11-11 shows the ICSP programming details for reading all of the configuration memory. Note that the TBLPAG register is hard-coded to 0xF8 (the upper byte address of configuration memory), and the read pointer W6 is initialized to 0x0000.

**TABLE 11-11: SERIAL INSTRUCTION EXECUTION FOR READING ALL CONFIGURATION MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG, and the read pointer (W6) and the write pointer (W7) for TBLRD instruction.</b>		
0000	200F80	MOV #0xF8, W0
0000	880190	MOV W0, TBLPAG
0000	EB0300	CLR W6
0000	EB0380	CLR W7
0000	000000	NOP
<b>Step 3: Read the Configuration register and write it to the VISI register (located at 0x784).</b>		
0000	BA0BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	883C20	MOV W0, VISI
0000	000000	NOP
<b>Step 4: Output the VISI register using the REGOUT command.</b>		
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
<b>Step 5: Reset device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6: Repeat steps 3-5 six times to read all of configuration memory.</b>		

# dsPIC30F Flash Programming Specification

## 11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

**TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.</b>		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
<b>Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.</b>		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 4: Output W0:W5 using the VISI register and REGOUT command.</b>		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
<b>Step 5: Reset device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6: Repeat steps 3-5 until all desired data memory is read.</b>		

# dsPIC30F Flash Programming Specification

## 11.13 Reading the Application ID Word

The application ID word is stored at address 0x8005BE in executive code memory. To read this memory location, you must use the SIX control code to move this program memory location to the VISI register. The REGOUT control code must then be used to clock the contents of the VISI register out of the device. The corresponding control and instruction codes that must be serially transmitted to the device to perform this operation are shown in [Table 11-13](#).

Once the programmer has clocked-out the application ID word, it must be inspected. If the application ID has the value 0xBB, the programming executive is resident in memory and the device can be programmed using the mechanism described in [Section 5.0 “Device Programming”](#). However, if the application ID has any other value, the programming executive is not resident in memory. It must be loaded to memory before the device can be programmed. The procedure for loading the programming executive to the memory is described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

## 11.14 Exiting ICSP Mode

After confirming that the programming executive is resident in memory, or loading the programming executive, ICSP mode is exited by removing power to the device or bringing MCLR to V<sub>IL</sub>. Programming can then take place by following the procedure outlined in [Section 5.0 “Device Programming”](#).

**TABLE 11-13: SERIAL INSTRUCTION EXECUTION FOR READING THE APPLICATION ID WORD**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W0) for TBLRD instruction.</b>		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	205BE0	MOV #0x5BE, W0
0000	207841	MOV VISI, W1
0000	000000	NOP
0000	BA0890	TBLRDL [W0], [W1]
0000	000000	NOP
0000	000000	NOP
<b>Step 3: Output the VISI register using the REGOUT command.</b>		
0001	<VISI>	Clock out contents of the VISI register
0000	000000	NOP

# dsPIC30F Flash Programming Specification

**TABLE A-1: CHECKSUM COMPUTATION (CONTINUED)**

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F5016	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6015	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404

**Item Description:**

**SUM(a:b)** = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

**CFGB** = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

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**Note the following details of the code protection feature on Microchip devices:**

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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